

L Number	Hits	Search Text	DB	Time stamp
1	4951	(427/96,145,240).CCLS.	USPAT; US-PGPUB; EP ; JP ; DERWENT	2003/09/22 10:46
2	271	((427/96,145,240).CCLS.) and (resist or photoresist) and (ARC or BARC or reflect\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/22 10:47
3	88	((427/96,145,240).CCLS.) and (resist or photoresist) and (ARC or BARC or reflect\$5)) and ((wafer or substrate) same edge)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/22 10:48
-	1756	(430/30).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/21 13:59
-	115	((430/30).CCLS.) and (wafer with edge)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/21 14:01
-	66	((430/30).CCLS.) and (wafer with edge)) and (ARC or reflect\$4) and (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/21 14:18
-	5883	(430/311-313,322).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/21 14:18
-	412	((430/311-313,322).CCLS.) and wafer and ((edge with (bead or expos\$4)) and (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/21 14:51
-	423	((430/311-313,322).CCLS.) and wafer and ((edge with (bead or expos\$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/21 14:20
-	195	((430/311-313,322).CCLS.) and wafer and ((edge with (bead or expos\$4))) and ((ARC or reflect\$5) and (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/21 14:56
-	539	(356/237.4-237.6).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/21 14:50
-	7	((356/237.4-237.6).CCLS.) and wafer and ((edge with (bead or expos\$4)) and (resist or photoresist))	USPAT; US-PGPUB; EP ; JP ; DERWENT	2003/09/21 14:53
-	2602	(resist or photoresist) and ((wafer or substrate or Silicon) and (edge near (bead\$3 or trim\$4 or expos\$5)))	USPAT; US-PGPUB; EP ; JP ; DERWENT	2003/09/21 14:56

-	859	((resist or photoresist) and ((wafer or substrate or Silicon) and (edge near (bead\$3 or trim\$4 or expos\$5)))) and ((ARC or reflect\$5) and (resist or photoresist))	USPAT; US-PGPUB; EP ; JP ; DERWENT	2003/09/21 14:56
-	286	((resist or photoresist) and ((wafer or substrate or Silicon) and (edge near (bead\$3 or trim\$4 or expos\$5)))) and ((ARC or reflect\$5) and (resist or photoresist)) and ((wafer or substrate or Silicon) with (edge near (bead\$3 or trim\$4 or expos\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/21 14:57